

## **I. Amendments to the Specification**

Please replace paragraph [0019] with the following amended paragraph:

**[0019]** As noted, it is a feature of the second p-type semiconductor layer 16 that it includes a graded doping concentration. The presence of dopants in the second p-type semiconductor layer 16 is controlled in order to optimize the performance of the photodiode. A first concentration 15 is located near the first p-type semiconductor 14, and a second concentration 17 is directly adjacent to the n-type semiconductor 18. Preferably, ~~the first concentration 15~~ D is between 800 and 1,000 angstroms deep, i.e. the dimension parallel to the travel of the carriers.

Please replace paragraph [0020] with the following amended paragraph:

**[0020]** In the preferred embodiment, the first concentration 15 is greater than the second concentration 17. In particular, the first concentration 15 is located at a position  $x_0$  and defines a dopant concentration  $p_0$ . A preferred doping concentration gradient is governed by the following equation:

$$(1) \quad p = p_0 e^{\frac{-x}{D}}$$

over the depth D of the second p-type semiconductor layer 16 for all x and D greater than zero. ~~A graph representative of Equation (1) is shown in Figure 4.~~ A generic representation of the dopant concentration  $p$  is shown in Figure 4.

Please replace paragraph [0024] with the following amended paragraph:

**[0024]** Another aspect of the graded doping concentration of the second p-type semiconductor layer 16 is the creation of a pseudo-electric field. The electrons generated in the first concentration 15 region are subject to this pseudo-field shown below as

$$(2) \quad E = \left( \frac{kT}{q} \right) \frac{dp}{dx},$$

$$(2) \quad E = - \left( \frac{kT}{q} \right) \frac{dp}{dx} \frac{1}{p}$$

where k is Boltzman's constant, T is the temperature, q is the charge of an electron, and the value  $\frac{dp}{dx}$  is the doping concentration gradient.